

## PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-346668

(43)Date of publication of application : 27.12.1993

(51)Int.Cl. G03F 7/039  
 G03F 7/004  
 G03F 7/027  
 H01L 21/027

(21)Application number : 04-156818

(71)Applicant : FUJITSU LTD

(22)Date of filing : 16.06.1992

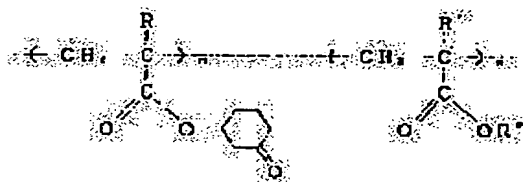
(72)Inventor : NOZAKI KOJI  
 TAKECHI SATOSHI  
 KAIMOTO HIROKO

## (54) RESIST COMPOSITION AND PATTERN FORMING METHOD USING IT

## (57)Abstract:

PURPOSE: To provide a radiation resist compsn. having high sensitivity and dry etching resistance by incorporating a copolymer containing 3-oxocyclohexyl acrylate or methacrylate monomers as the repeating unit.

CONSTITUTION: This radiation resist compsn. contains a copolymer expressed by formula having 3-oxocyclohexyl acrylate or methacrylate monomer unit, and preferably, other acrylate or methacrylate monomer unit as the repeating unit. In formula, R and R' are H or CH<sub>3</sub> and R'' is an org. acid. If this compsn. is prepared to obtain a resist material, R'' is preferably an alicyclic org. group, for example, adamantyl group, norbornyl group, or cyclohexyl group in order to obtain small absorption in a short wavelength region and high dry etching durability. The weight average mol.wt. of this copolymer is preferably 2000 to 3000000.



## LEGAL STATUS

[Date of request for examination] 11.12.1998

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number] 3236073

[Date of registration] 28.09.2001

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's  
decision of rejection]

[Date of extinction of right]

Copyright (C); 1998,2003 Japan Patent Office